

Supplementary Information for
Anisotropic thermoelectric properties of layered compounds
in SnX₂ (X = S, Se): A promising thermoelectric

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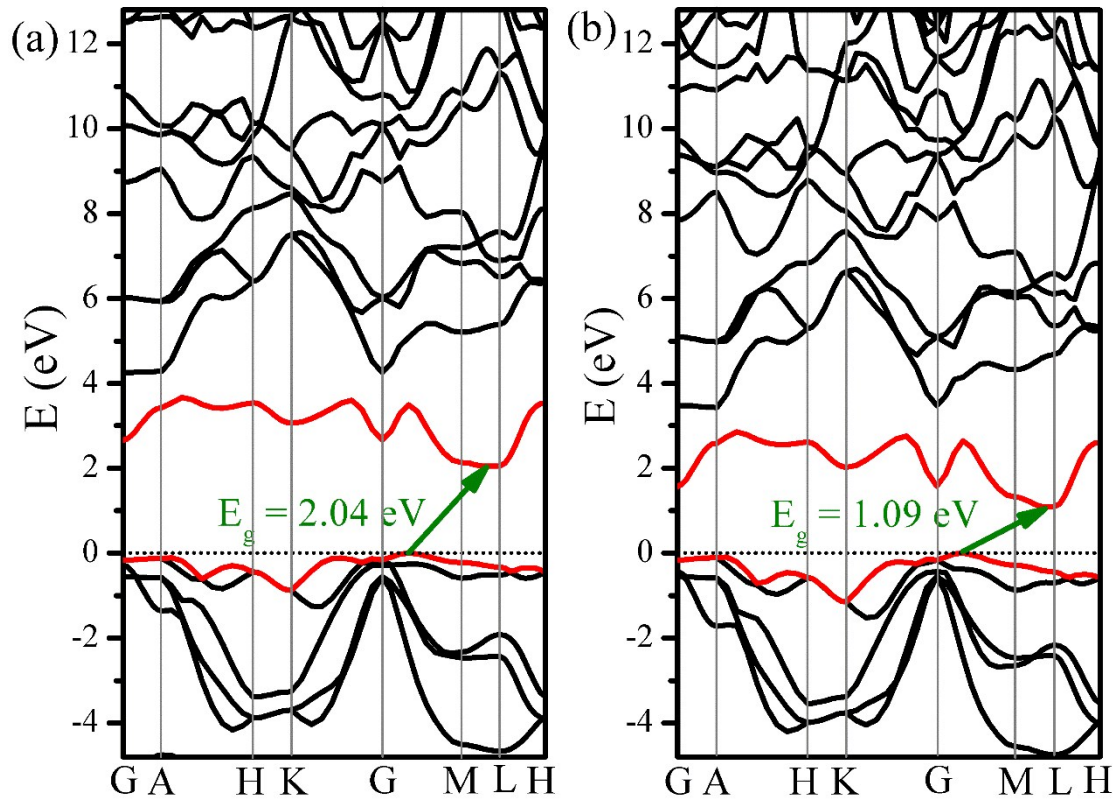


Fig. S1. Band structures of SnS₂ (a) and SnSe₂ (b). Top of the valence band is set to zero. The highest valence band and lowest conduction band are highlighted in red. G , A , H , K , M , L are $(0\ 0\ 0)$, $(0\ 0\ 0.5)$, $(-0.333\ 0.667\ 0.5)$, $(-0.333\ 0.667\ 0)$, $(0\ 0.5\ 0)$, $(0\ 0.5\ 0.5)$ high symmetry points, respectively.

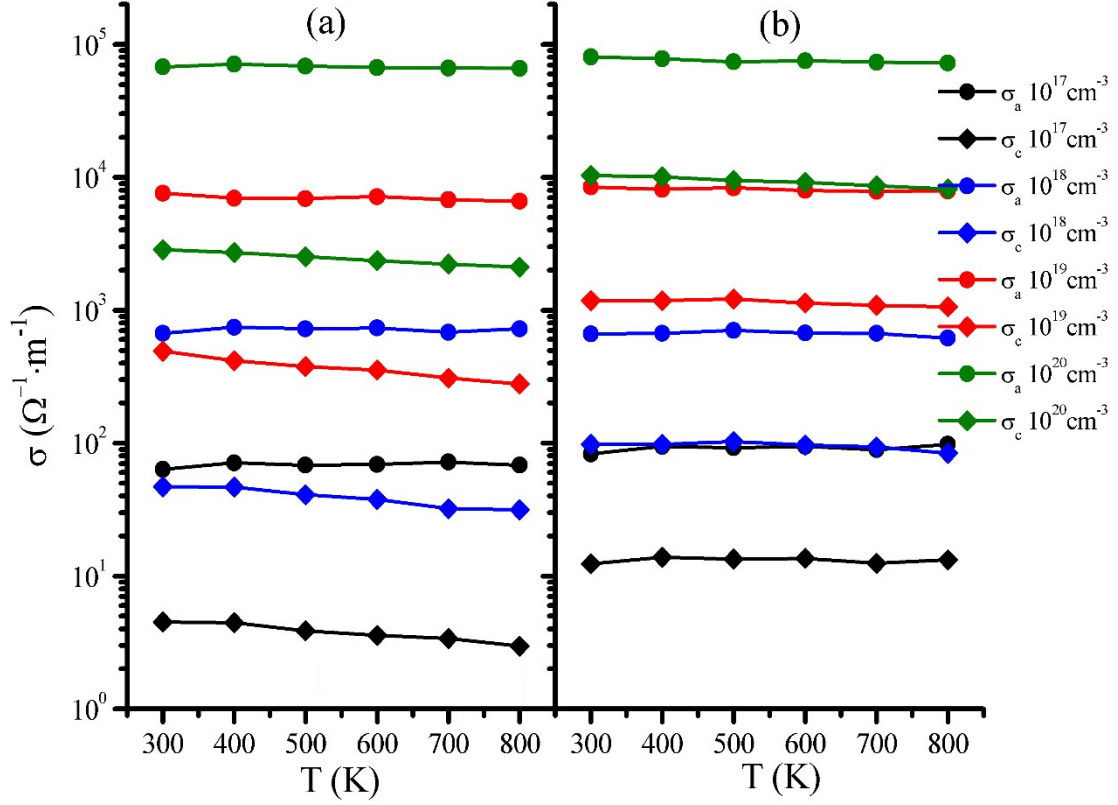


Fig. S2. Temperature dependence of the electrical conductivities along the a (σ_a) and c (σ_c) directions in SnS_2 (a) and SnSe_2 (b) for four different carrier concentrations.

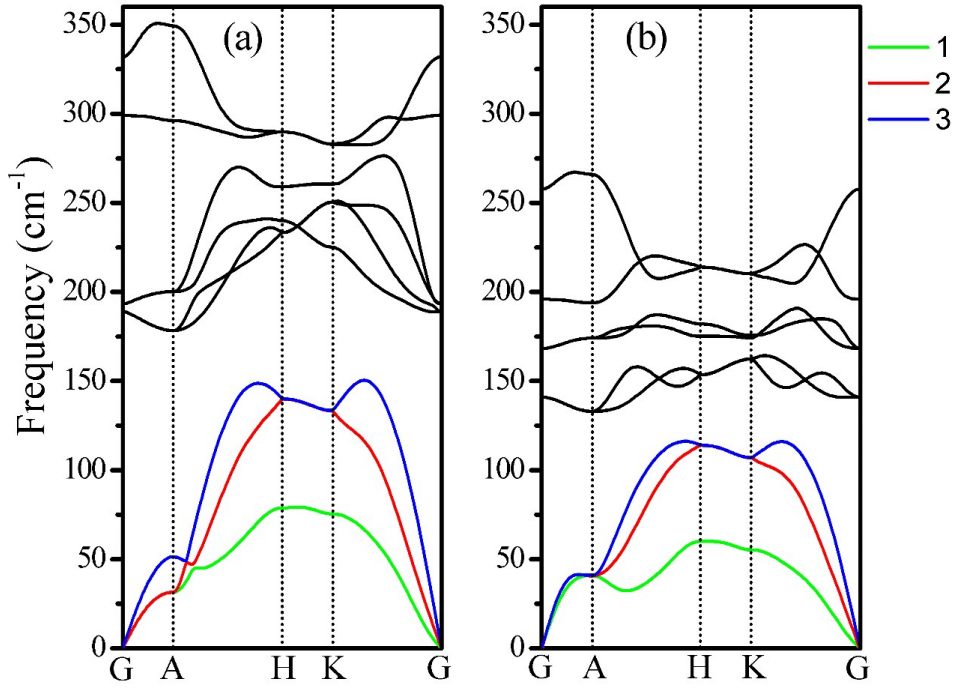


Fig. S3. Phonon dispersion of SnS_2 (a) and SnSe_2 (b). Three acoustic phonon branches are indicated with different colors.

Table S1 Debye temperatures (Θ) and phonon velocities (v) along the a and c axes for SnS₂ and SnSe₂.

SnS ₂			SnSe ₂		
GK/a	Θ (K)	v (m/s)	GK/a	Θ (K)	v (m/s)
1	108	1538	1	80	1327
2	191	2902	2	153	2878
3	216	5289	3	167	4452
Average	172	3243	Average	133	2886
GA/c	Θ (K)	v (m/s)	GA/c	Θ (K)	v (m/s)
1	45	1904	1	59	2120
2	45	1903	2	60	2270
3	74	2899	3	60	2270
Average	55	2235	Average	60	2220

Values are calculated from the phonon dispersions (Figure S3). The Debye temperature is calculated using $\Theta = \omega_D/k_B$ (ω_D is the largest acoustic frequency in each direction); the phonon velocity is the slope of the acoustic phonon dispersion around the G point.